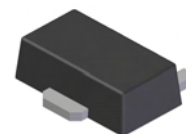
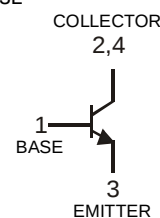
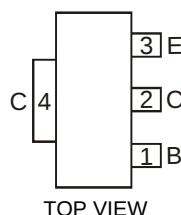


Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DXT5401)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**



SOT89-3L



Schematic and Pin Configuration

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish - Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	600	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation @T _A = 25°C (Note 3)	P _D	1	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 3)	R _{θJA}	125	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	180	—	V	I _C = 100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	160	—	V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	—	V	I _E = 10μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	50	nA	V _{CB} = 120V, I _E = 0
Emitter Cutoff Current	I _{EBO}	—	50	nA	V _{CB} = 120V, I _E = 0, T _A = 100°C
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h _{FE}	80	—	—	V _{CE} = 5.0V, I _C = 1.0mA
		80	250	—	V _{CE} = 5.0V, I _C = 10mA
		30	—	—	V _{CE} = 5.0V, I _C = 50mA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	0.15	V	I _C = 10mA, I _B = 1.0mA
		—	0.20	V	I _C = 50mA, I _B = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	1.0	V	I _C = 10mA, I _B = 1.0mA
		—	—	V	I _C = 50mA, I _B = 5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	6.0	pF	V _{CB} = 10V, f = 1.0MHz, I _E = 0
Small Signal Current Gain	h _{fe}	50	200	—	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f _T	100	300	MHz	V _{CE} = 10V, I _C = 10mA, f = 100MHz
Noise Figure	NF	—	8.0	dB	V _{CE} = 5.0V, I _C = 200μA, R _S = 1.0kΩ, f = 1.0kHz

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤ 2%.

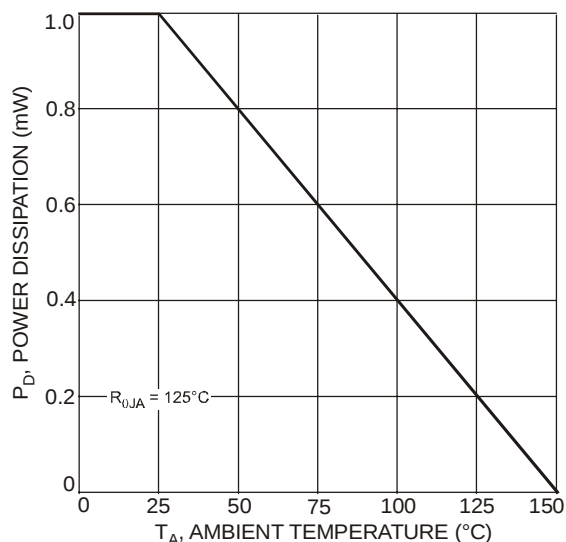


Fig. 1 Max Power Dissipation vs. Ambient Temperature

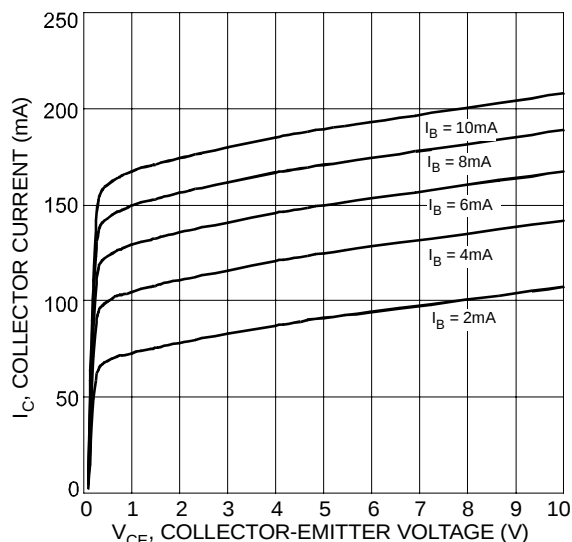


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

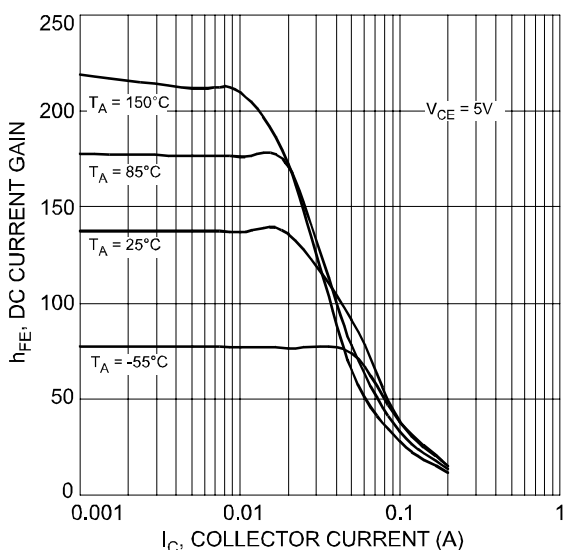


Fig. 3 Typical DC Current Gain vs. Collector Current

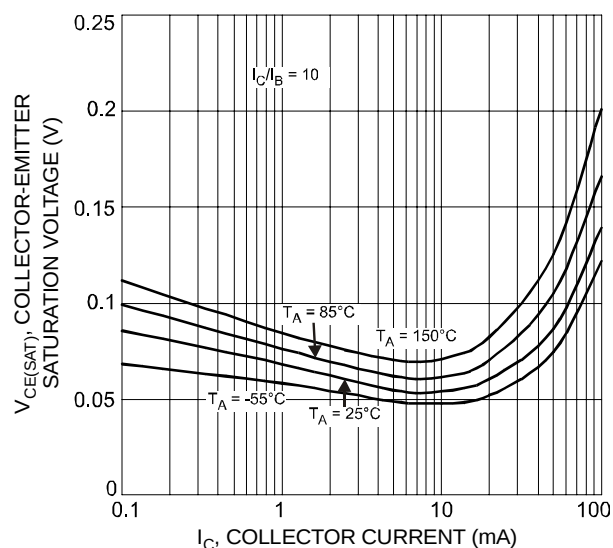


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

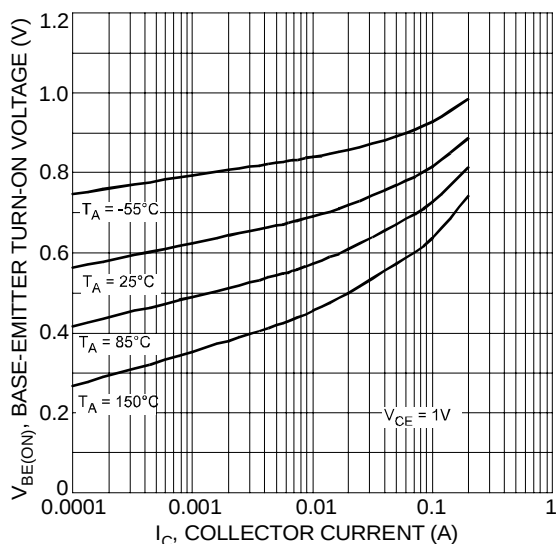


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

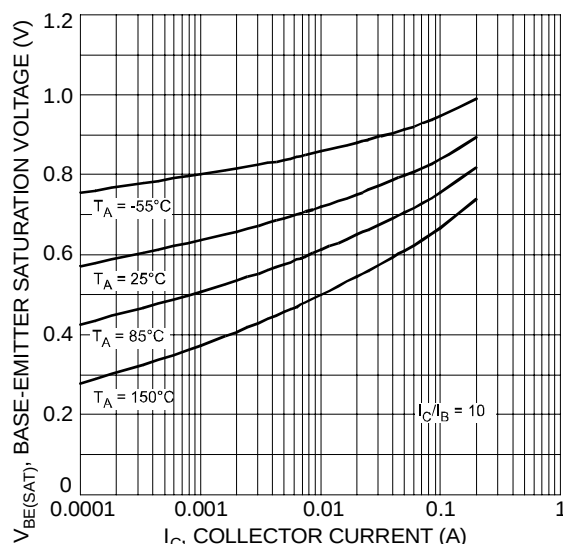


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

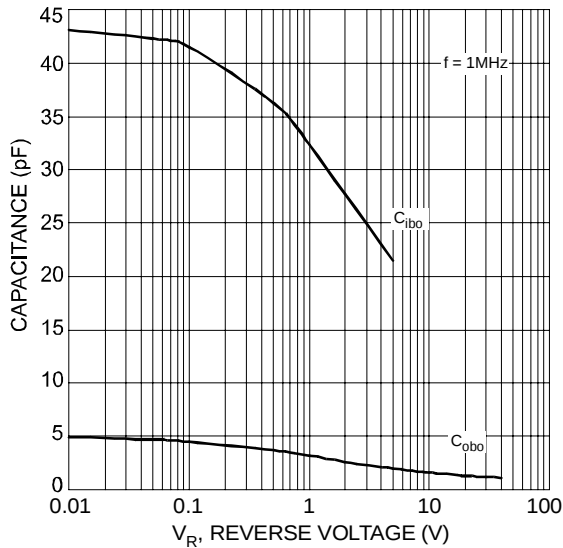


Fig. 7 Typical Capacitance Characteristics

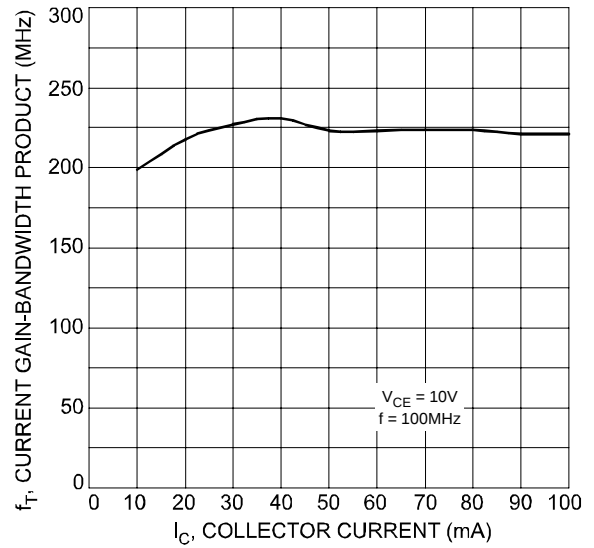


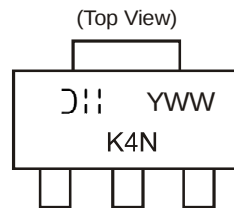
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DXT5551-13	SOT89-3L	2500/Tape & Reel

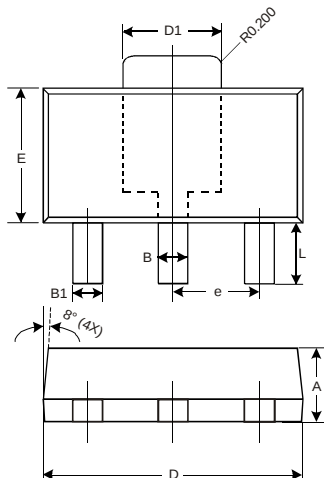
Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



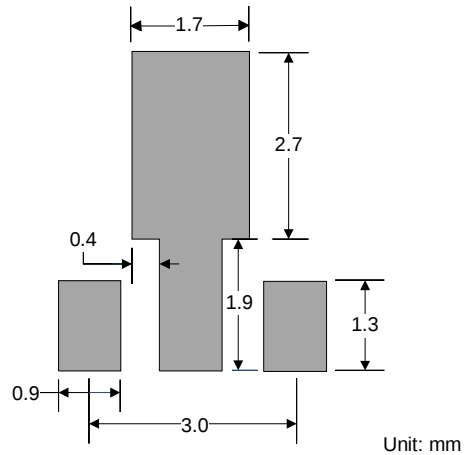
311 = Manufacturer's code marking
K4N = Product type marking code
YWW = Date code marking
Y = Last digit of year ex: 7 = 2007
WW = Week code 01 - 52

Package Outline Dimensions



SOT89-3L			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

Suggested Pad Layout



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<http://moschip.ru/get-element>

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